

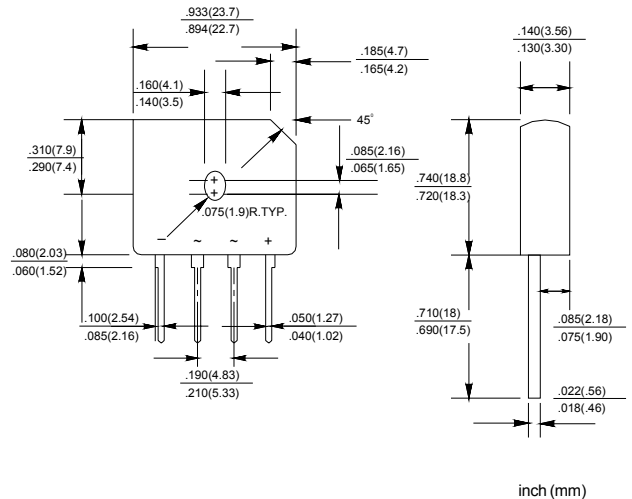
## SILICON BRIDGE RECTIFIERS

VOLTAGE RANGE: 50 --- 1000 V  
CURRENT: 35.0 A

### FEATURES

- ◇ Rating to 1000V PRV
- ◇ 400 Amperes surge capability
- ◇ High efficiency
- ◇ Electrically isolated metal case for maximum heat dissipation
- ◇ Mounting: thru hole for # 8 screw Mounting
- ◇ Glass passivated chip junctions

### GBU35



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

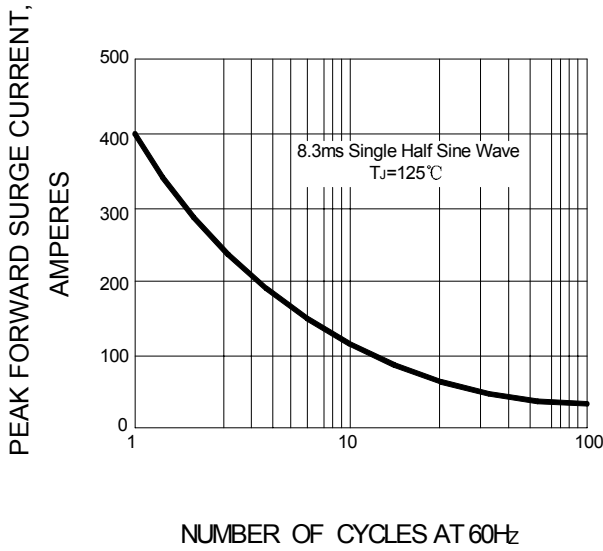
Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

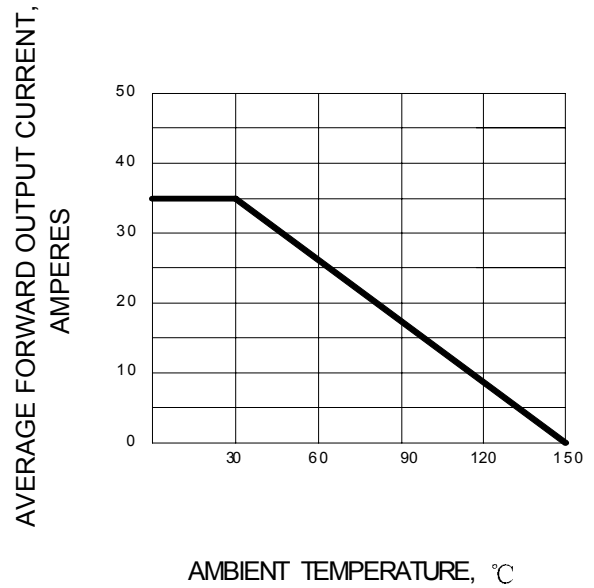
		GBU 35A	GBU 35B	GBU 35D	GBU 35G	GBU 35J	GBU 35K	GBU 35M	UNITS
Maximum recurrent peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_A=25^\circ\text{C}$	$I_{F(AV)}$	35.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	$I_{FSM}$	400.0							A
Maximum instantaneous forward voltage @ 17.5 A	$V_F$	1.1							V
Maximum reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	$I_R$	10.0 1.0							$\mu\text{A}$ mA
Operating junction temperature range	$T_J$	- 55 ---- + 155							°C
Storage temperature range	$T_{STG}$	- 55 ---- + 150							°C

www.galaxycn.com

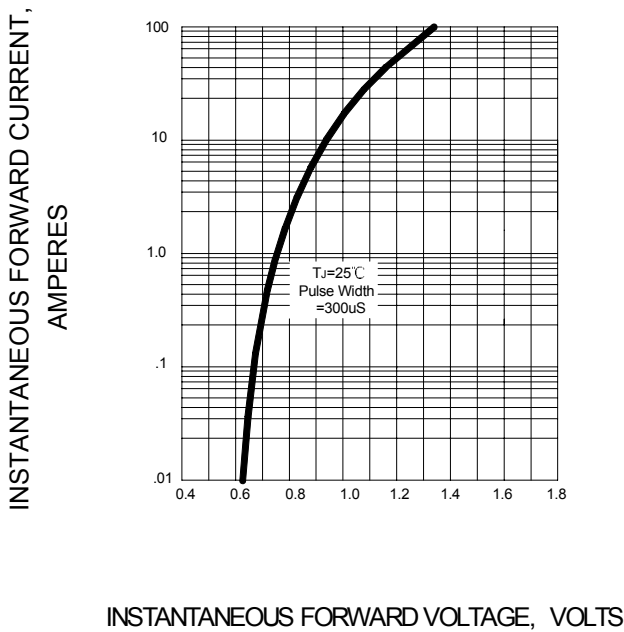
**FIG.1 – PEAK FORWARD SURGE CURRENT**



**FIG.2 – FORWARD DERATING CURVE**



**FIG.3 – TYPICAL FORWARD CHARACTERISTIC**



**FIG.4 – TYPICAL REVERSE CHARACTERISTIC**

